

ABSTRACT

Light Pattern Exposure Method, Photomask, and Photomask Blank

5

A light pattern exposure method is by irradiating ArF excimer laser light to a resist film through a photomask. The photomask includes a transparent substrate and a pattern of optical film of a material comprising a transition metal,
10 silicon, nitrogen and oxygen, with contents thereof falling in a specific range. The photomask may be irradiated with ArF excimer laser light in a cumulative dose of at least 10 kJ/cm².

Fig 1